

Description

The HSCB3010 is the high cell density trench N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

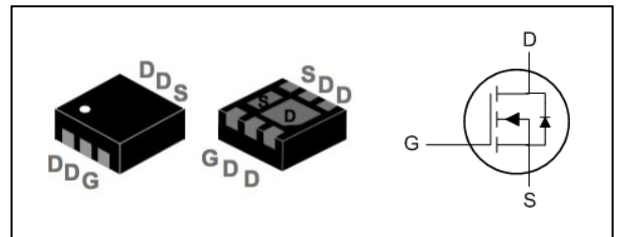
The HSCB3010 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V _{DS}	30	V
R _{DS(ON),typ}	7.5	mΩ
I _D	20	A

DFN2*2-6L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V ₁	20	A
I _D @T _A =100°C	Continuous Drain Current, V _{GS} @ 10V ₁	13	A
I _{DM}	Pulsed Drain Current ₂	80	A
EAS	Single Pulse Avalanche Energy ₃	16	mJ
P _D @T _A =25°C	Total Power Dissipation ₄	6.2	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJC}	Thermal Resistance Junction-Case ₁	---	20	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
B _{VDS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔB _{VDS} /ΔT _J	B _{VDS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.027	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ₂	V _{GS} =10V, I _D =20A	---	7.5	10	mΩ
		V _{GS} =4.5V, I _D =10A	---	11.5	17	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1	1.5	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.8	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V, V _{GS} =10V, I _D =20A	---	19	---	nC
Q _{gs}	Gate-Source Charge		---	6.4	---	
Q _{gd}	Gate-Drain Charge		---	5	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =3Ω I _D =10A	---	7	---	ns
T _r	Rise Time		---	6	---	
T _{d(off)}	Turn-Off Delay Time		---	26	---	
T _f	Fall Time		---	7	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	950	---	pF
C _{oss}	Output Capacitance		---	140	---	
C _{rss}	Reverse Transfer Capacitance		---	120	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current _{1,5}	V _G =V _D =0V, Force Current	---	---	20	A
I _{SM}	Pulsed Source Current _{2,5}		---	---	80	A
V _{SD}	Diode Forward Voltage ₂	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =20A, di/dt=100A/μs,	---	7	---	nS
Q _{rr}	Reverse Recovery Charge	T _J =25°C	---	6.5	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.5mH, R_G=25R
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.



Typical Characteristics

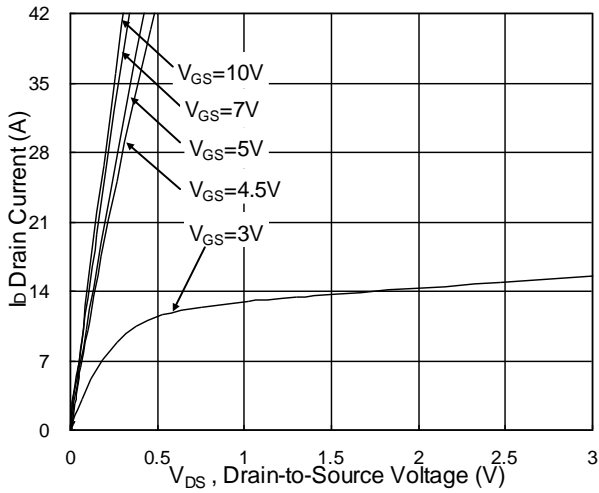


Fig.1 Typical Output Characteristics

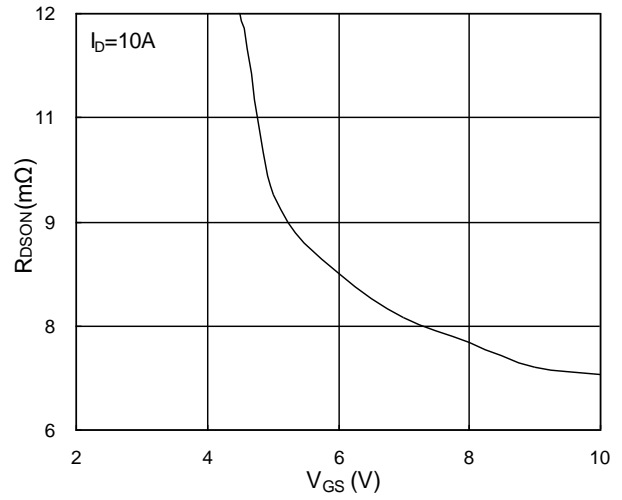


Fig.2 On-Resistance vs. Gate-Source

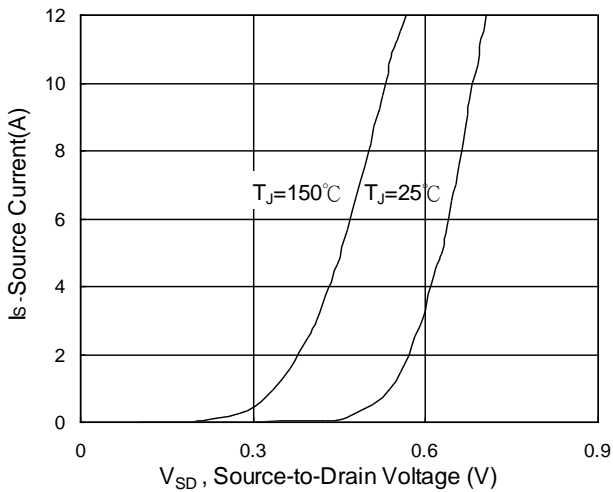


Fig.3 Forward Characteristics of reverse

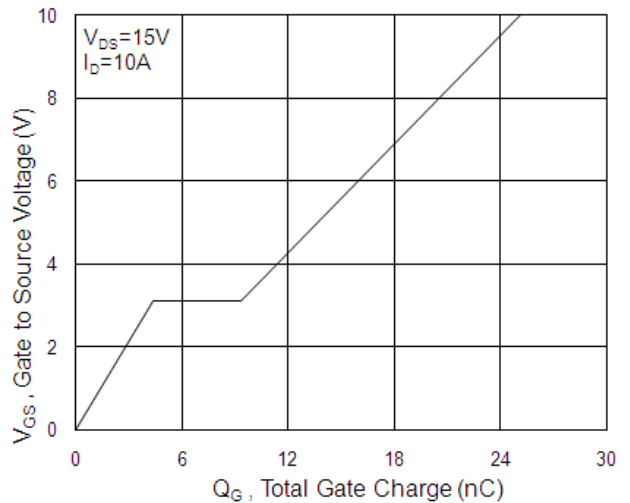


Fig.4 Gate-Charge Characteristics

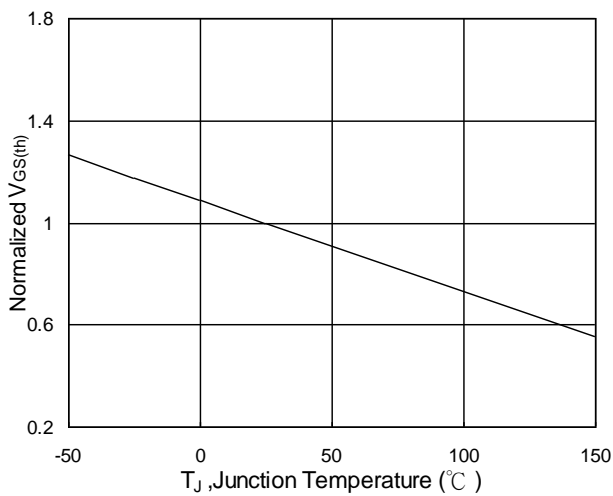


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

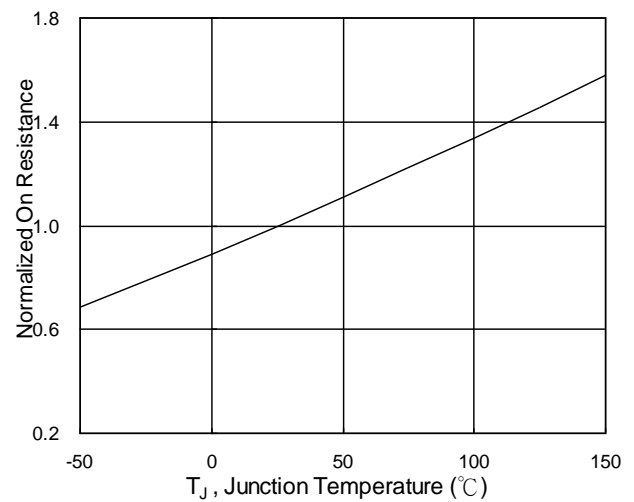


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

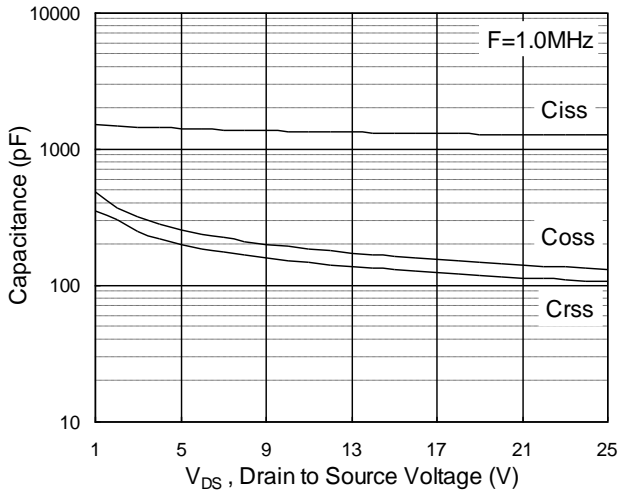


Fig.7 Capacitance

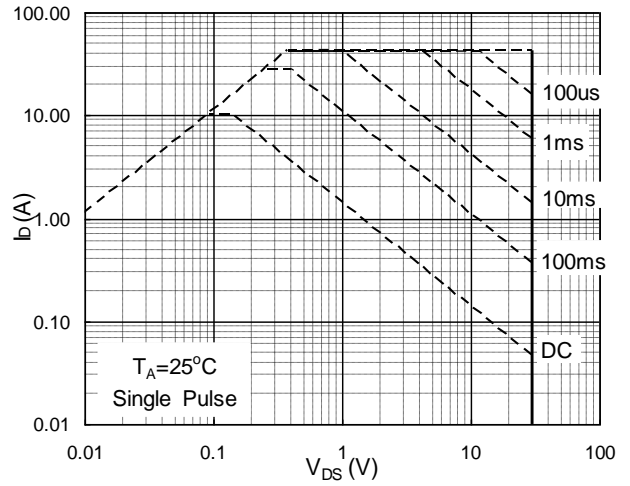


Fig.8 Safe Operating Area

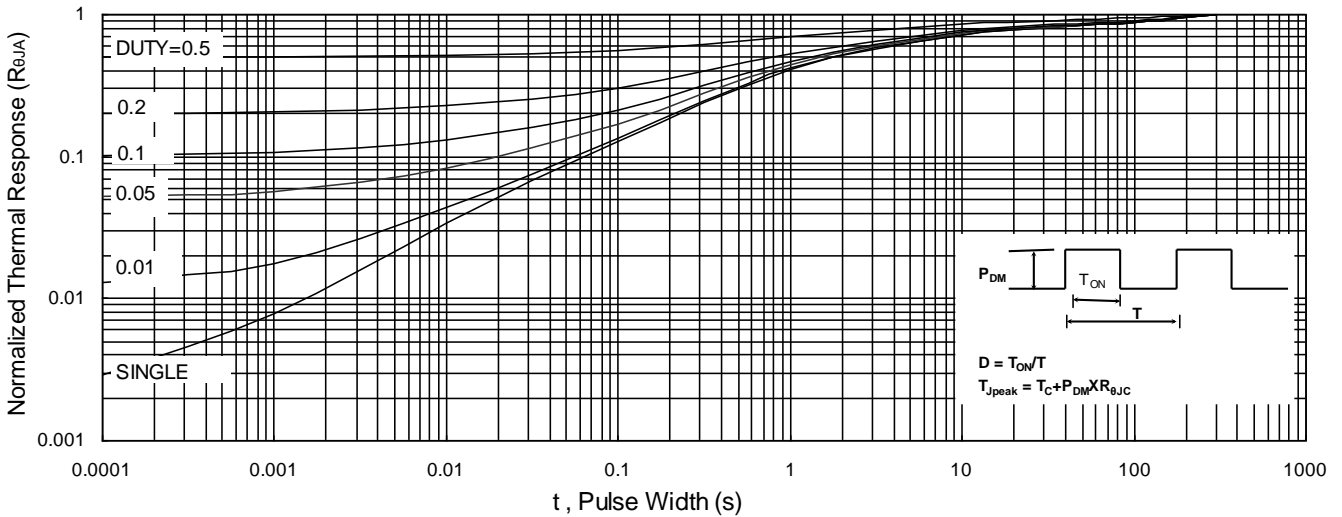


Fig.9 Normalized Maximum Transient Thermal Impedance

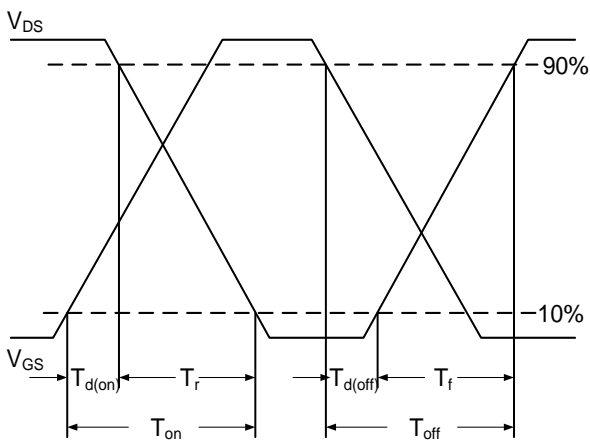


Fig.10 Switching Time Waveform

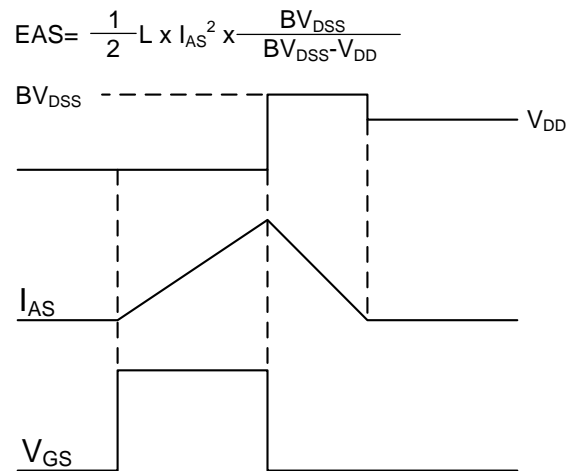
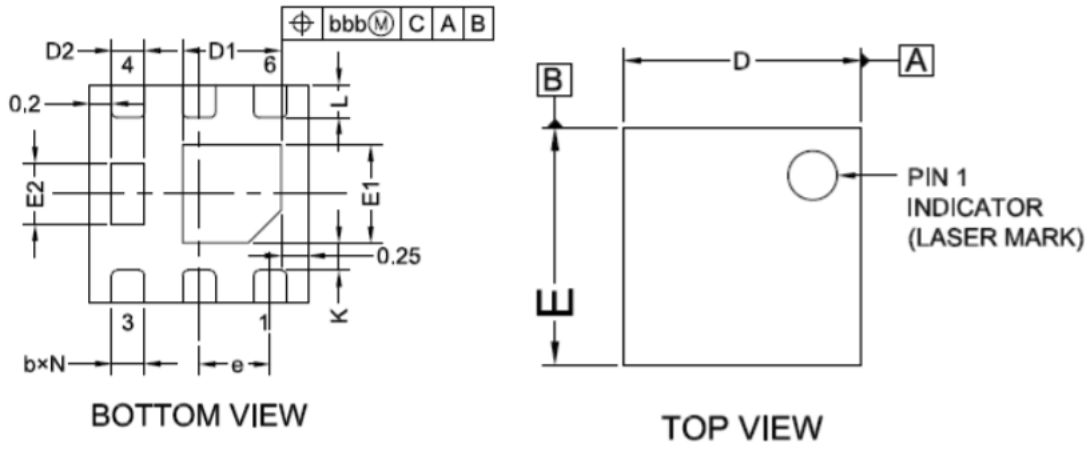


Fig.11 Unclamped Inductive Switching

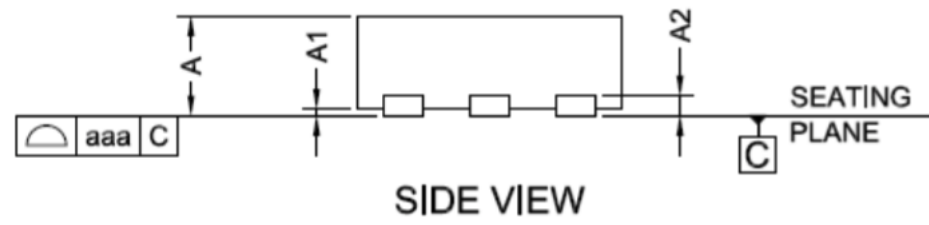


DFN2x2-6L 2EP PACKAGE INFORMATION



BOTTOM VIEW

TOP VIEW



SIDE VIEW

**COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)**

SYMBOL	MIN	TYP	MAX
A	0.50	0.55	0.60
A1	0.00	0.02	0.05
A2	0.152REF.		
b	0.25	0.30	0.35
D	1.95	2.00	2.05
D1	0.80	0.90	1.00
D2	0.25	0.30	0.35
E	1.95	2.00	2.05
E1	0.80	0.90	1.00
E2	0.46	0.56	0.66
e	0.65BSC		
L	0.25	0.30	0.35
J	0.40BSC		
K	0.20MIN		
N	6		
aaa	0.08		
bbb	0.10		